

PMN80XP

20 V, single P-channel Trench MOSFET Rev. 1 — 8 May 2012

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- R_{DSon} specified at 1.8 V operation
- Trench MOSFET technology
- Fast switching

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-	-3.2	Α
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.5 \text{ A}; T_j = 25 \text{ °C}$		-	80	102	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Pinning information

Table 2. **Pinning information**

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	D. D. D.	
2	D	drain	<u> </u>	D
3	G	gate		
4	S	source	1 12 13	
5	D	drain	SOT457 (TSOP6)	S 017aaa257
6	D	drain		• · · · · · · · · · · · · · · · · · · ·



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3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMN80XP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457	

4. Marking

Table 4. Marking codes

Type number	Marking code
PMN80XP	WA

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	Symbol	Parameter	Conditions		Min	Max	Unit
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V_{DS}	drain-source voltage	T _{amb} = 25 °C		-	-20	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V_{GS}	gate-source voltage			-12	12	V
$V_{GS} = -4.5 \text{ V; } T_{amb} = 100 \text{ °C} \qquad \begin{array}{ c c c c }\hline 11 & - & -1.6 & A \\ \hline I_{DM} & \text{peak drain current} & T_{amb} = 25 \text{ °C; single pulse; } t_p \leq 10 \text{ µs} & - & -10 & A \\ \hline P_{tot} & \text{total power dissipation} & T_{amb} = 25 \text{ °C} & \begin{array}{ c c c }\hline 12 & - & 385 & m \\ \hline \hline 11 & - & 925 & m \\ \hline \hline T_{sp} = 25 \text{ °C} & - & 4000 & m \\ \hline \hline T_{amb} & \text{ambient temperature} & -55 & 150 & \text{°C} \\ \hline T_{stg} & \text{storage temperature} & -65 & 150 & \text{°C} \\ \hline Source-drain diode & & & & \\ \hline \end{array}$	I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-3.2	Α
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			V _{GS} = -4.5 V; T _{amb} = 25 °C	<u>[1]</u>	-	-2.5	Α
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			V _{GS} = -4.5 V; T _{amb} = 100 °C	<u>[1]</u>	-	-1.6	Α
	I _{DM}	peak drain current	$T_{amb} = 25$ °C; single pulse; $t_p \le 10 \mu s$		-	-10	Α
$T_{sp} = 25 ^{\circ}\text{C} \qquad \qquad - \qquad 4000 \text{m}$ $T_{j} \qquad \text{junction temperature} \qquad \qquad -55 150 ^{\circ}\text{C}$ $T_{amb} \qquad \text{ambient temperature} \qquad \qquad -55 150 ^{\circ}\text{C}$ $T_{stg} \qquad \text{storage temperature} \qquad \qquad -65 150 ^{\circ}\text{C}$ $Source-drain diode$	P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	385	mW
Tjjunction temperature-55150°CTambambient temperature-55150°CTstgstorage temperature-65150°CSource-drain diode				<u>[1]</u>	-	925	mW
T _{amb} ambient temperature -55 150 °C T _{stg} storage temperature -65 150 °C Source-drain diode			T _{sp} = 25 °C		-	4000	mW
T _{stg} storage temperature -65 150 °C Source-drain diode	Tj	junction temperature			-55	150	°C
Source-drain diode	T _{amb}	ambient temperature			-55	150	°C
	T _{stg}	storage temperature			-65	150	°C
	Source-drain	diode					
$T_{amb} = 25 ^{\circ}\text{C}$	Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-1	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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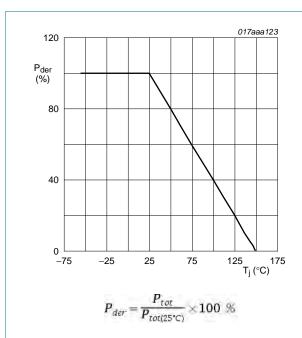


Fig 1. Normalized total power dissipation as a function of junction temperature

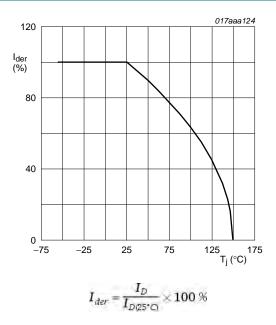
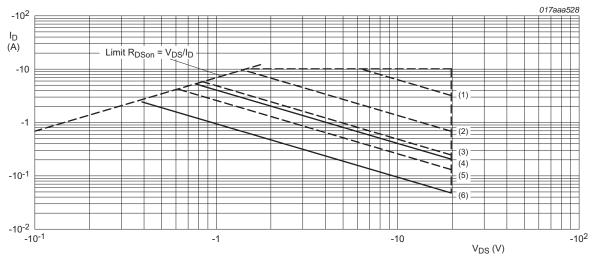


Fig 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

(1) $t_p = 100 \ \mu s$

(2) $t_p = 1 \text{ ms}$

(3) $t_p = 10 \text{ ms}$

(4) DC; $T_{sp} = 25$ °C

 $(5) t_p = 100 ms$

(6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 6 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

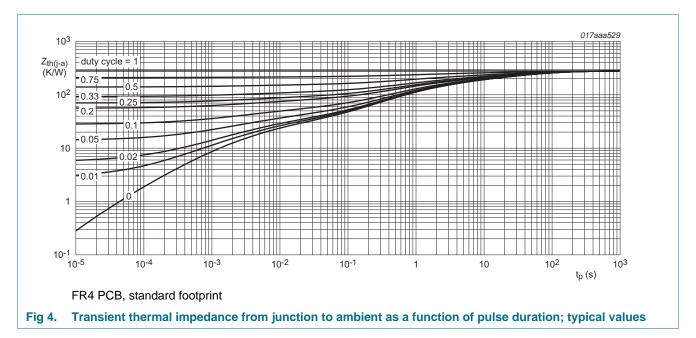
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6. Thermal characteristics

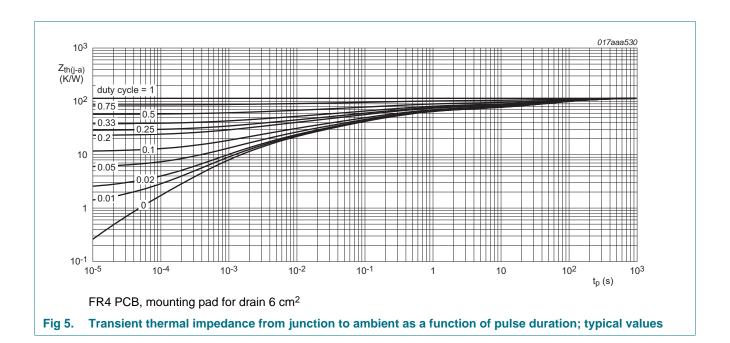
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	<u>[</u>	<u>[1]</u>	-	281	325	K/W
			[2]	-	116	135	K/W
			[3]	-	73	85	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	27	31	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², $t \le 5$ s



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7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.75	-1	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		V _{DS} = -20 V; V _{GS} = 0 V; T _{amb} = 150 °C	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2.5 \text{ A}; T_j = 25 \text{ °C}$	-	80	102	$m\Omega$
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.5 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	116	148	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -2.3 \text{ A}; T_j = 25 \text{ °C}$	-	95	125	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -1.1 \text{ A}; T_j = 25 \text{ °C}$	-	120	156	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -2.5 \text{ A}; T_j = 25 \text{ °C}$	-	15	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -2.5 A; V_{GS} = -4.5 V;	-	5	7.5	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.7	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	550	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	63	-	pF
C _{rss}	reverse transfer capacitance		-	53	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -2.5 A; V_{GS} = -4.5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	120	-	ns
t _f	fall time		-	50	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = -1.0 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.8	-1.2	V

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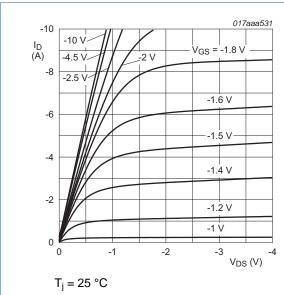


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

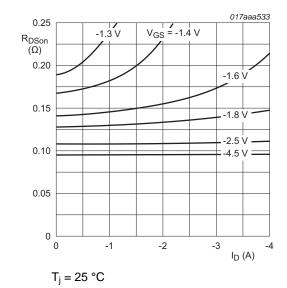


Fig 8. Drain-source on-state resistance as a function of drain current; typical values

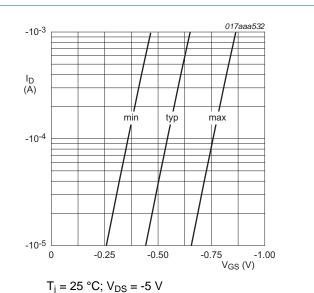


Fig 7. Sub-threshold drain current as a function of gate-source voltage

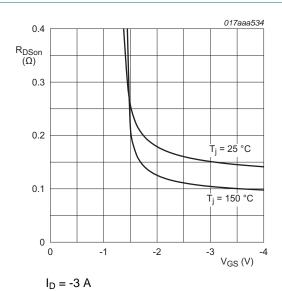


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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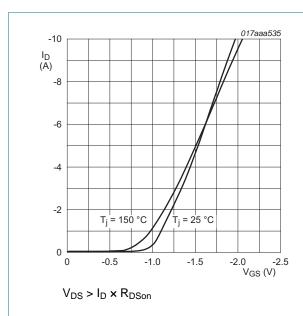


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

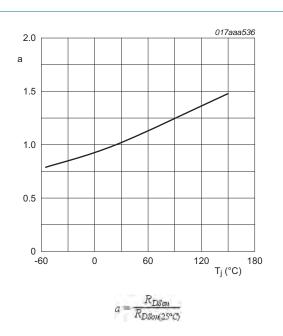


Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

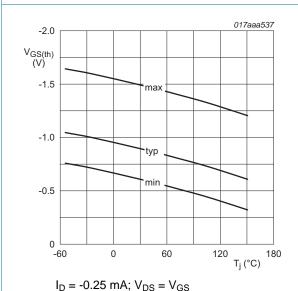
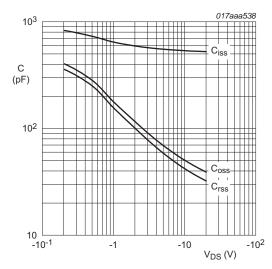


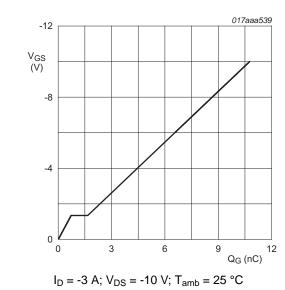
Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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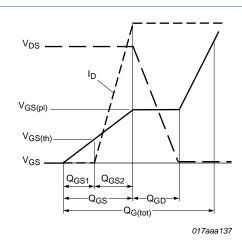
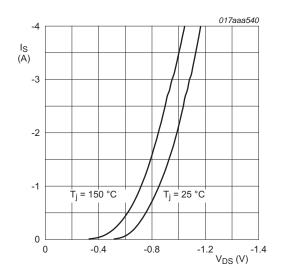


Fig 14. Gate charge waveform definitions

Fig 15. Gate charge waveform definitions

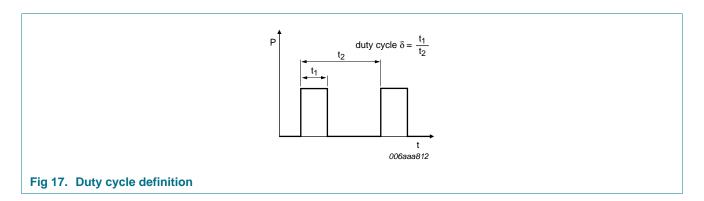


 $V_{GS} = 0 V$

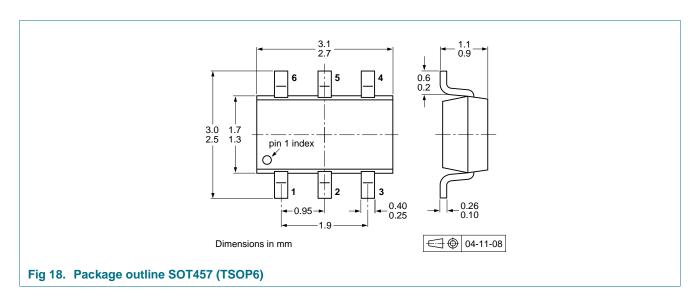
Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information

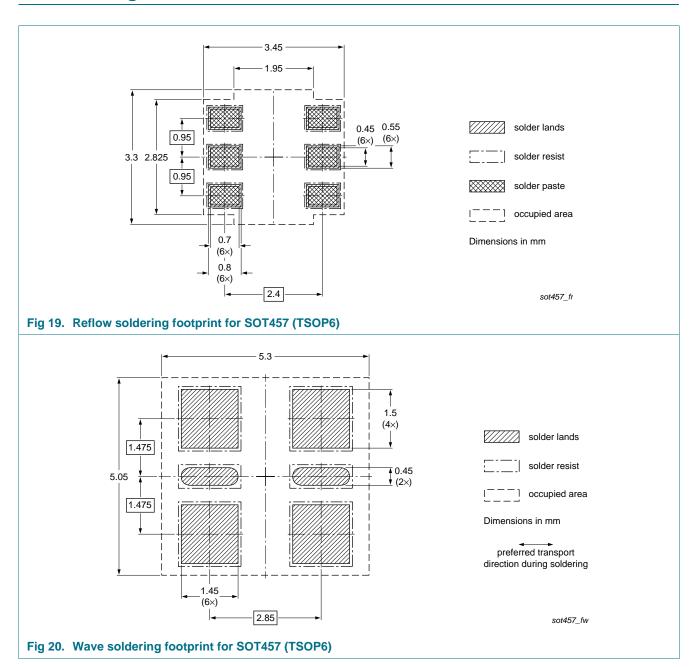


9. Package outline



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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMN80XP v.1	20120508	Product data sheet	-	-

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12. Legal information

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Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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